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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet 1 of 4

Complete if Known

Application Number	09/760,635
Filing Date	01/16/2001
First Named Inventor	Edmond, et al.
Group Art Unit	
Examiner Name	
Attorney Docket Number	5000.137

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
SWC	1	5,173,751		Ota et al.	12-22-1992	
	2	5,247,533		Okazaki et al.	09-21-1993	
	3	5,338,944		Edmond et al.	08-16-1994	
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TECHNOLOGY CENTER 2800**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₆
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SWC	28	KUBOTA, ET AL; "Preparation and properties of III-V nitride thin films"; J. Appl. Phys. 66(7); 1 October 1989; pp. 2984-2988	
	29	CHAN, ET AL.; "Metallization of GaN Thin Films Prepared by Ion Beam Assisted Molecular Beam Epitaxy"; Materials Research Society Symposium Proc. Vol. 339; 1994; pp. 223-227	
	30	LIN, ET AL.; "Low resistance ohmic contacts on wide band-gap GaN"; Appl. Phys. Lett. 64(8); 21 February 1994; pp. 1003-1005	
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	36	MONEMAR, ET AL; "Radiative recombination in In _{0.15} Ga _{0.85} N/GaN multiple quantum well structures"; MRS Internet Journal Nitride Semiconductor Research; 1999	
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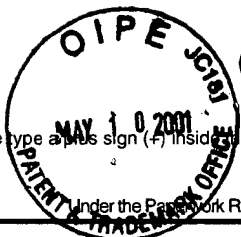
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SWC	39	KARIYA, ET AL; "Structural Properties of Al 1-x In x N Ternary Alloys on GaN Grown by Metalorganic Vapor Phase Epitaxy"; Jpn. Appl. Phys., Vol. 37; 1998; pp. 697-699	
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Application Number	09/760635
Filing Date	January 16, 2001
First Named Inventor	Edmond et al
Group Art Unit	2811
Examiner Name	
Attorney Docket Number	5000.137

Sheet	1	of	1
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